

Specifications	
Part Number	SI5475DC-T1-GE3
Manufacturer	Electro-Films (EFI) / Vishay
Description	MOSFET P-CH 12V 5.5A 1206-8
Category	Discrete Semiconductor Products > Transistors - FETs,
Part Status	2538 pcs Stock
Vgs(th) (Max) @ Id	450mV @ 1mA (Min)
Vgs (Max)	±8V
Technology	MOSFET (Metal Oxide)
Supplier Device Package	1206-8 ChipFET™
Series	TrenchFET®
Rds On (Max) @ Id, Vgs	31 mOhm @ 5.5A, 4.5V
Power Dissipation (Max)	1.3W (Ta)
Packaging	Tape & Reel (TR)
Package / Case	8-SMD, Flat Lead
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Surface Mount
Moisture Sensitivity Level (MSL)	1 (Unlimited)
Lead Free Status / RoHS Status	Lead free / RoHS Compliant
Gate Charge (Qg) (Max) @ Vgs	29nC @ 4.5V
FET Type	P-Channel
FET Feature	-
Drive Voltage (Max Rds On, Min Rds On)	1.8V, 4.5V
Drain to Source Voltage (Vdss)	12V
Detailed Description	P-Channel 12V 5.5A (Ta) 1.3W (Ta) Surface Mount
Current - Continuous Drain (Id) @ 25°C	5.5A (Ta)

In: SI5475DDC-T1-GE3 Vishay Siliconix MOSFET P-CH 12V 6A 1206-8	SI5475DDC-T1-E3 VISHAY VISHAY 1206-8	SI5475DC-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 5.5A 1206-8	SI5475DDC-T1-GE3 MOS VISHAY VISHAY 1206-8
SI5475DDC Vishay SI5475DDC Vishay	SI5475DC-T1-E3 Vishay Siliconix MOSFET P-CH 12V 5.5A 1206-8	SI5475DC VISHAY VISHAY SOT23-8	SI5475DDC-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 6A 1206-8

SI5475DC-T1-GE3 Electro-Films (EF1) / Vishay	SI5475DC-T1-GE3 Data Sheet	SI5475DC-T1-GE3 Datasheets	SI5475DC-T1-GE3 PDF	Electro-Films (EF1) / Vishay SI5475DC-T1-GE3
SI5475DC-T1-GE3 Electronic	SI5475DC-T1-GE3 Components	SI5475DC-T1-GE3 Distributor	SI5475DC-T1-GE3 Image	SI5475DC-T1-GE3 Part
SI5475DC-T1-GE3 Price	SI5475DC-T1-GE3 Manufacturer	SI5475DC-T1-GE3 Picture	SI5475DC-T1-GE3 Stock	SI5475DC-T1-GE3 Inventory
SI5475DC-T1-GE3 New	SI5475DC-T1-GE3 Original	SI5475DC-T1-GE3 Warranted	SI5475DC-T1-GE3 RFQ	SI5475DC-T1-GE3 Order Online